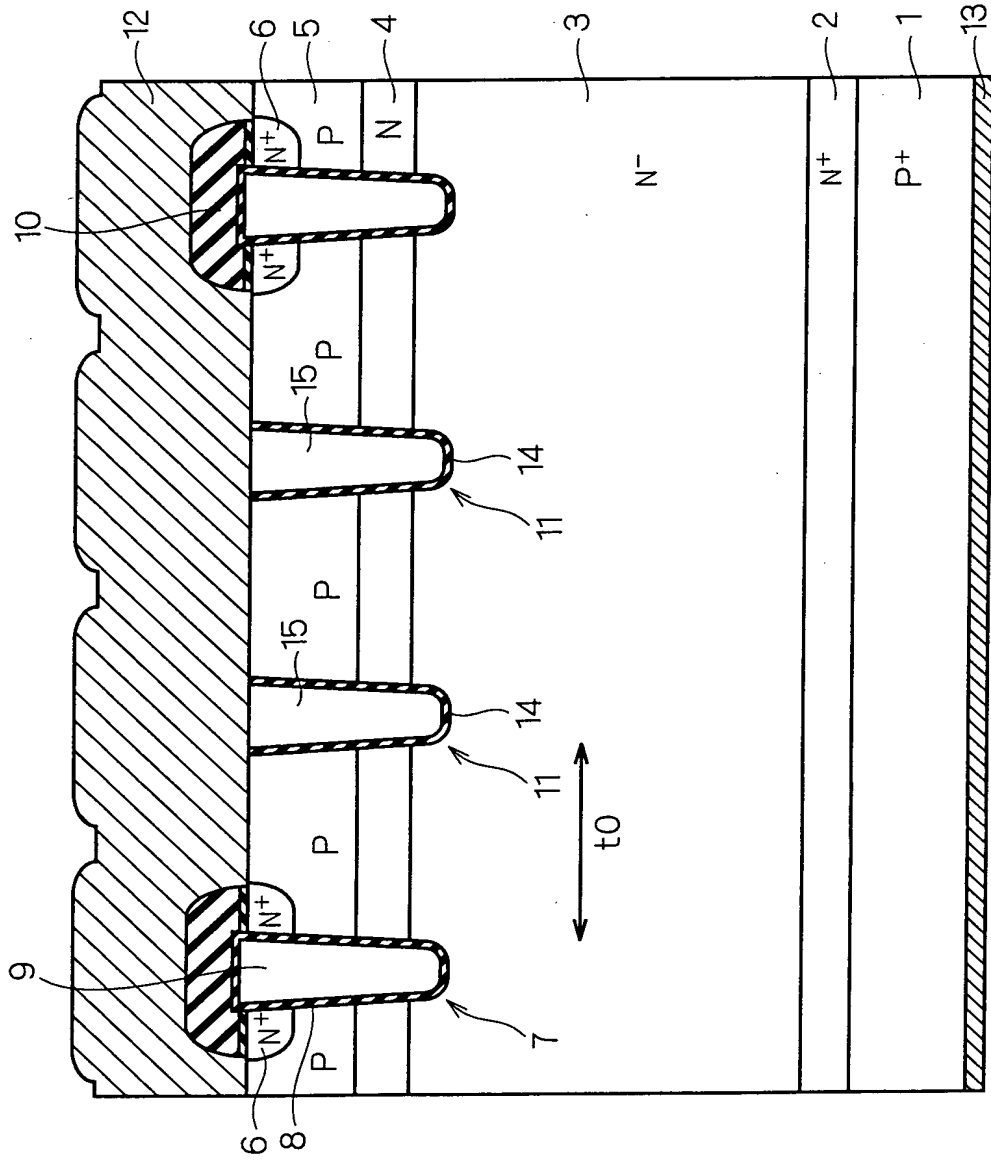
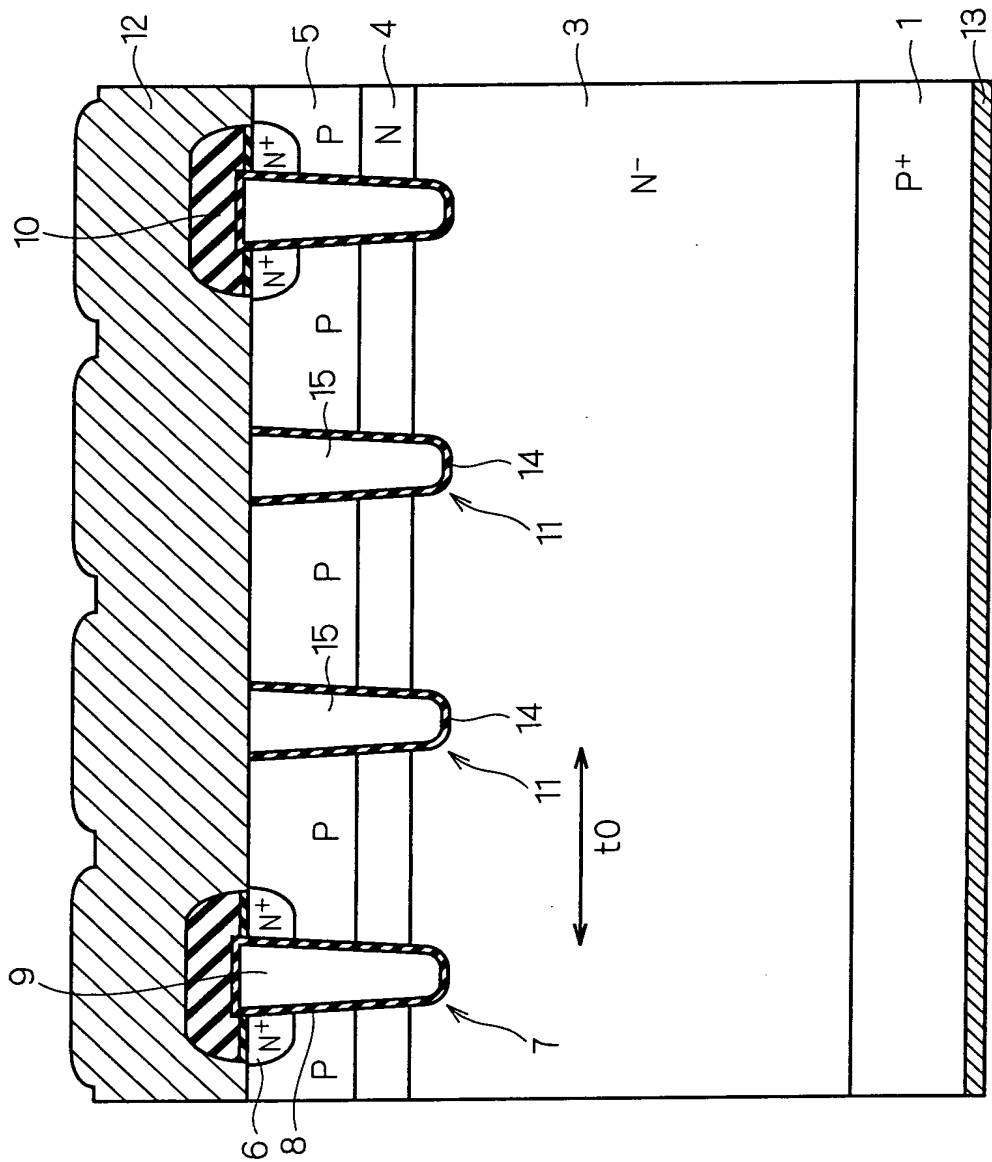


FIG. 1

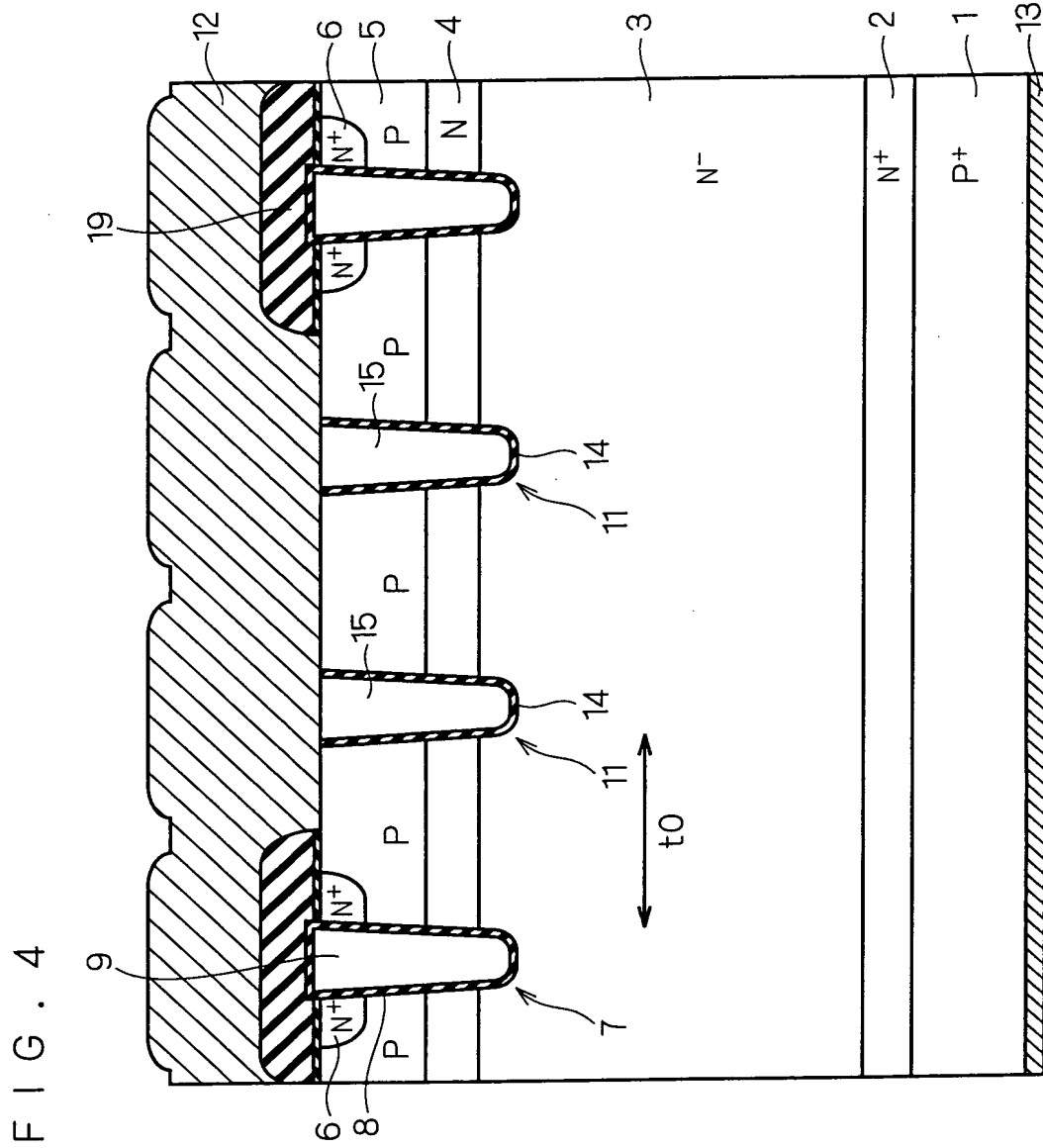


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FIG. 2



FOOT # 2293550



This diagram shows a cross-sectional view of a semiconductor device. The substrate consists of alternating layers of N⁺ and P-type material. A series of vertical structures are formed on the surface, labeled 1 through 19. A time axis t_0 is indicated by a double-headed arrow.

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FIG. 6

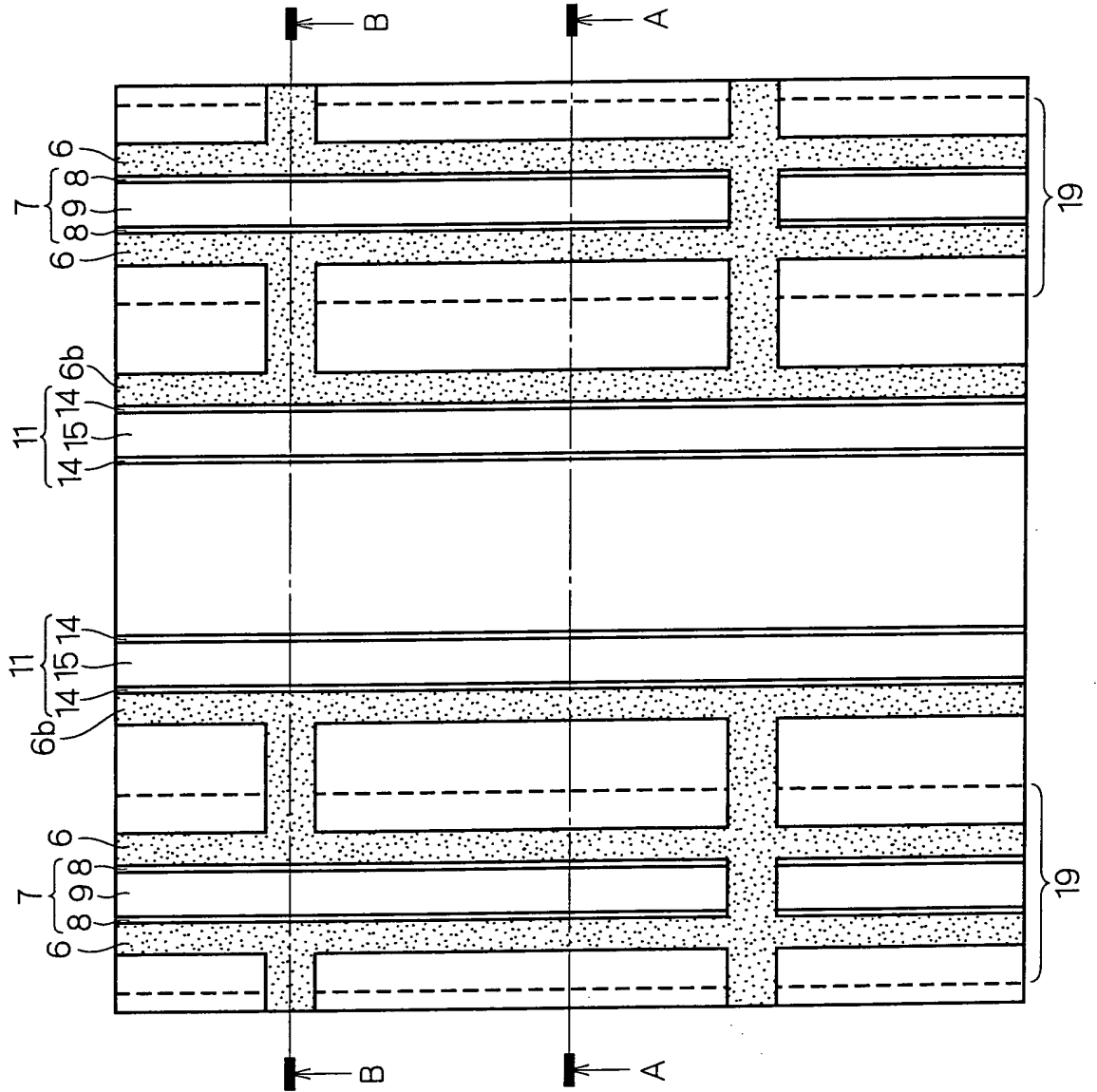


FIG. 7

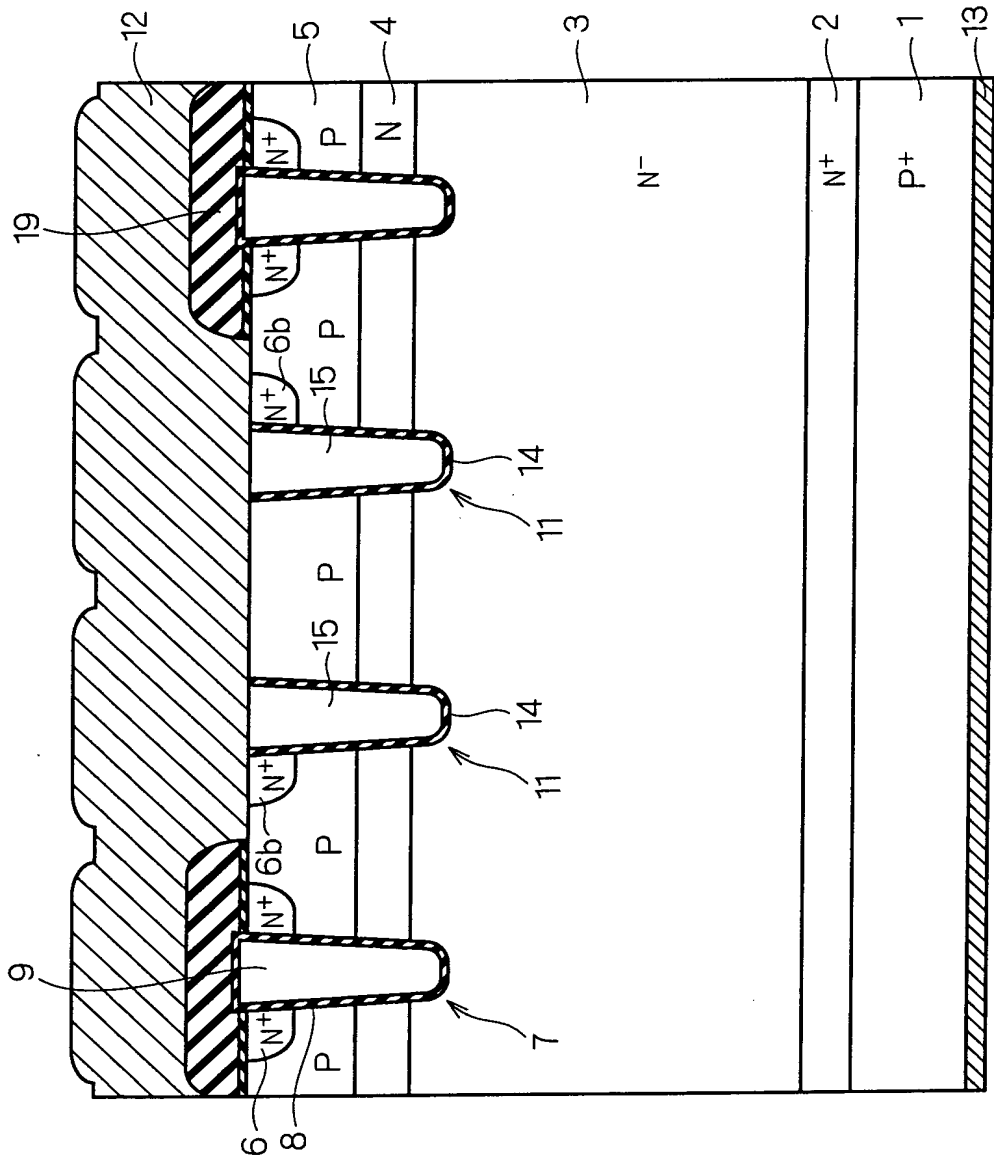


FIG. 7

FIG. 8

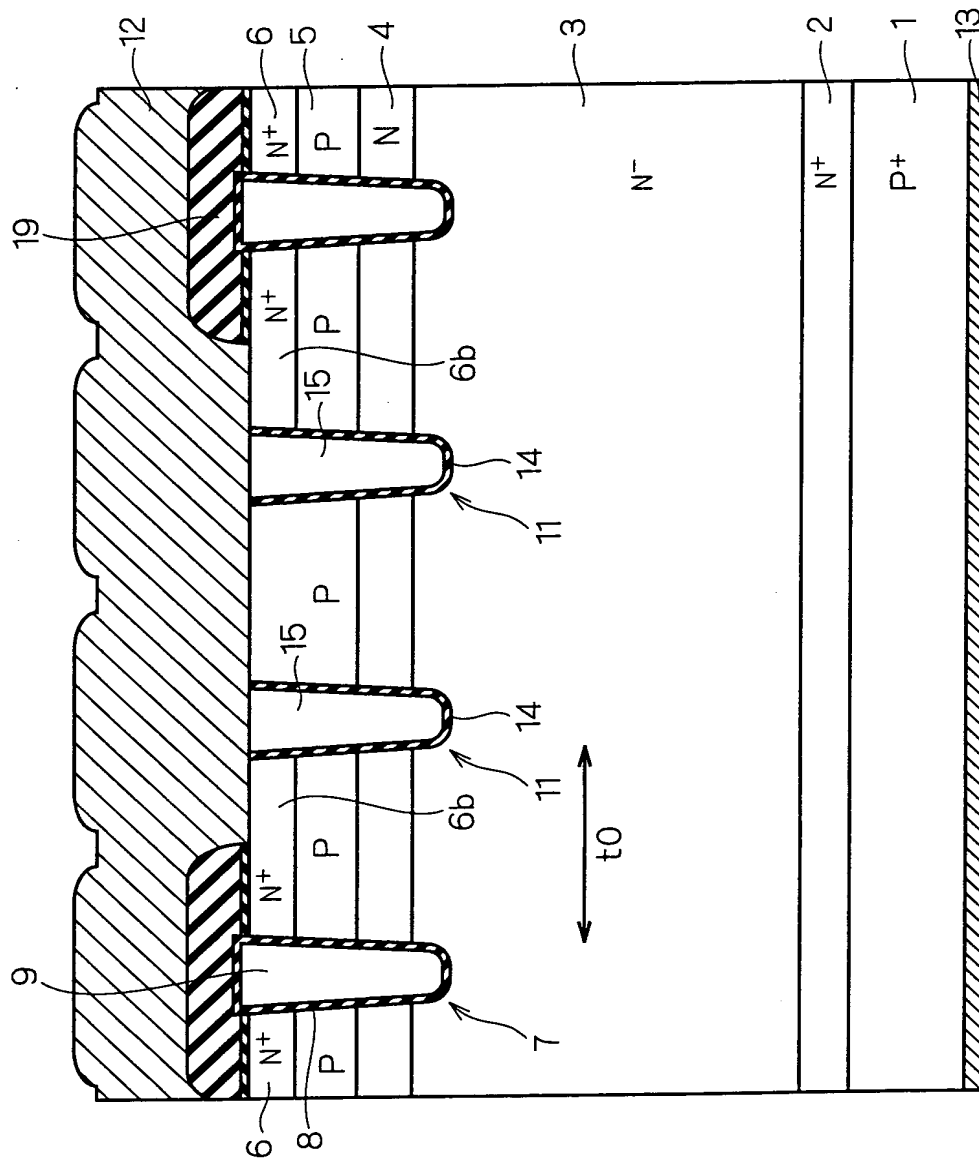


FIG. 8

FIG. 9

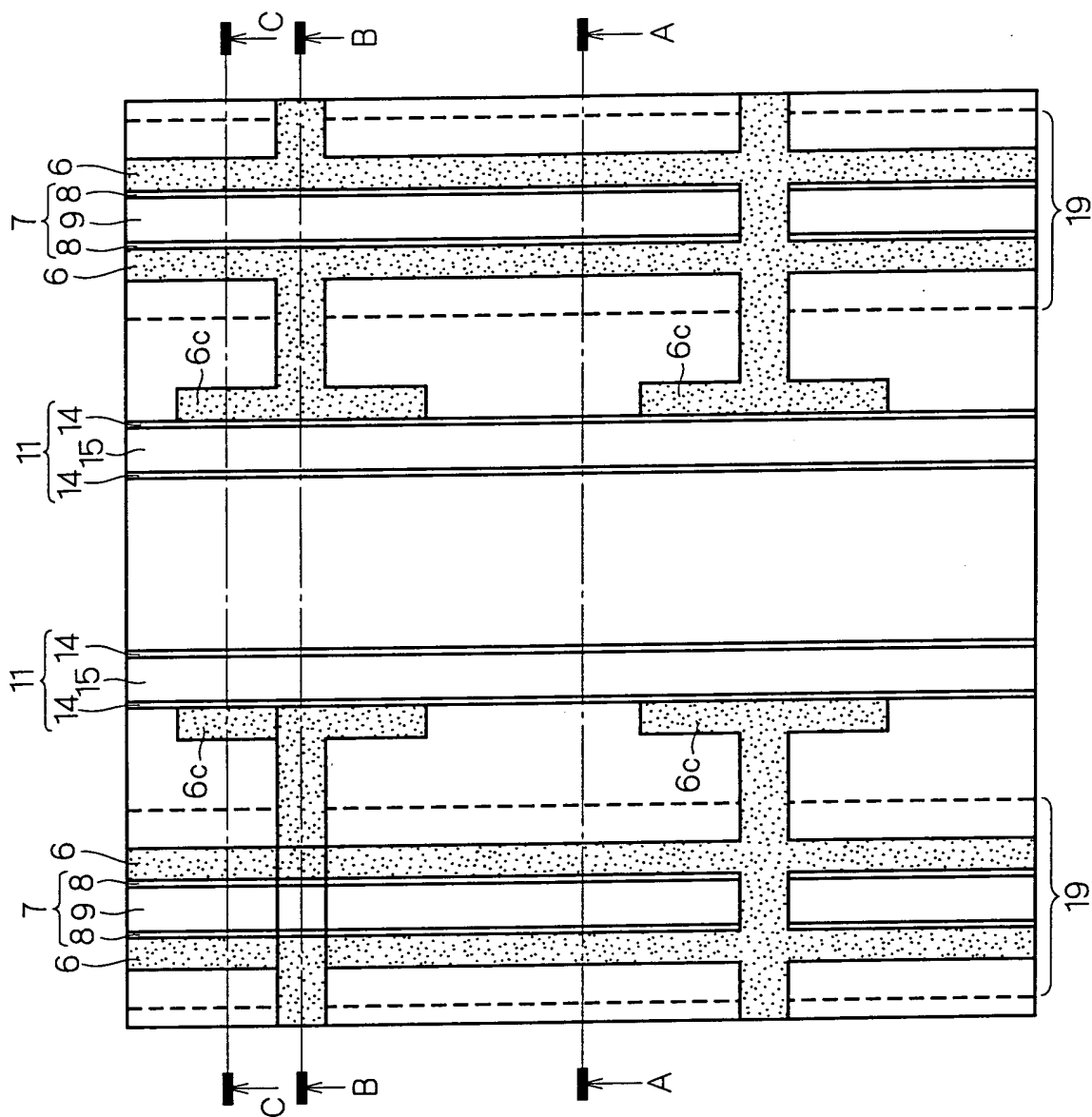


FIG. 9

[illegible]

FIG. 11

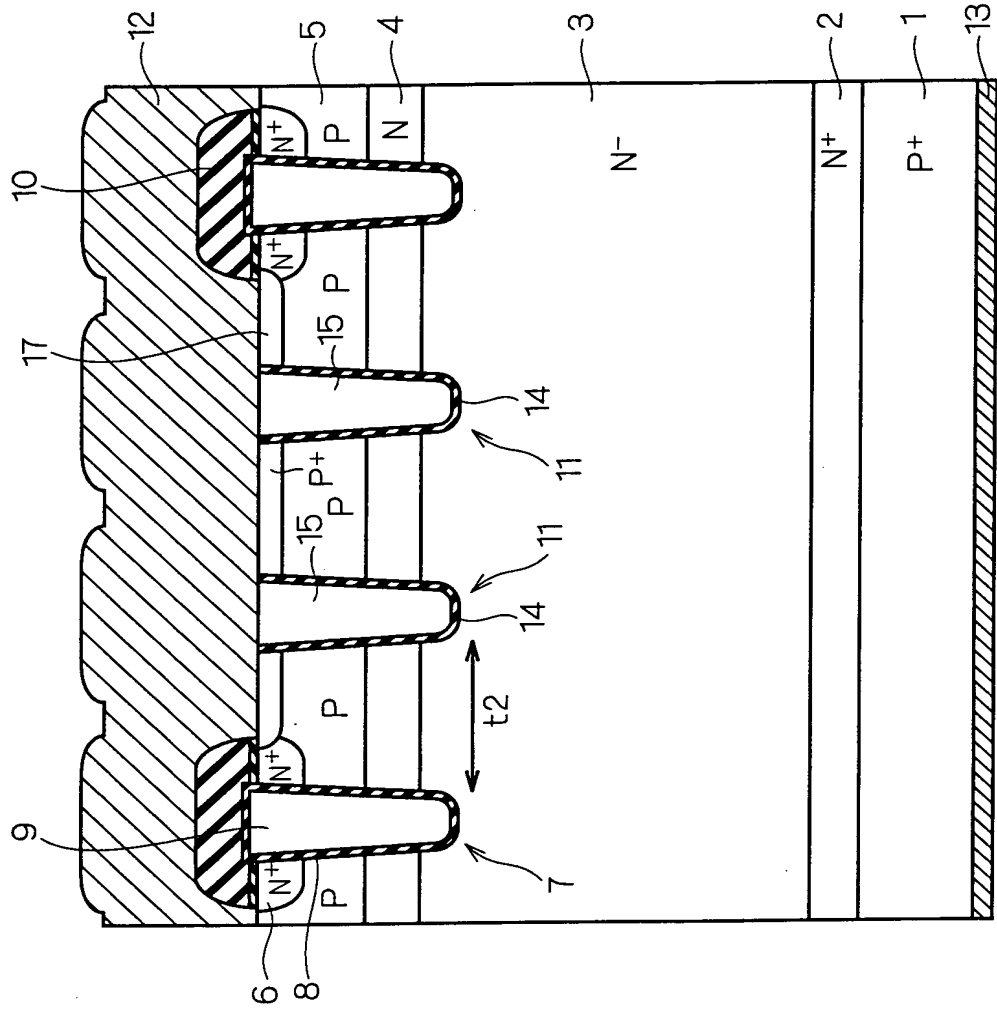
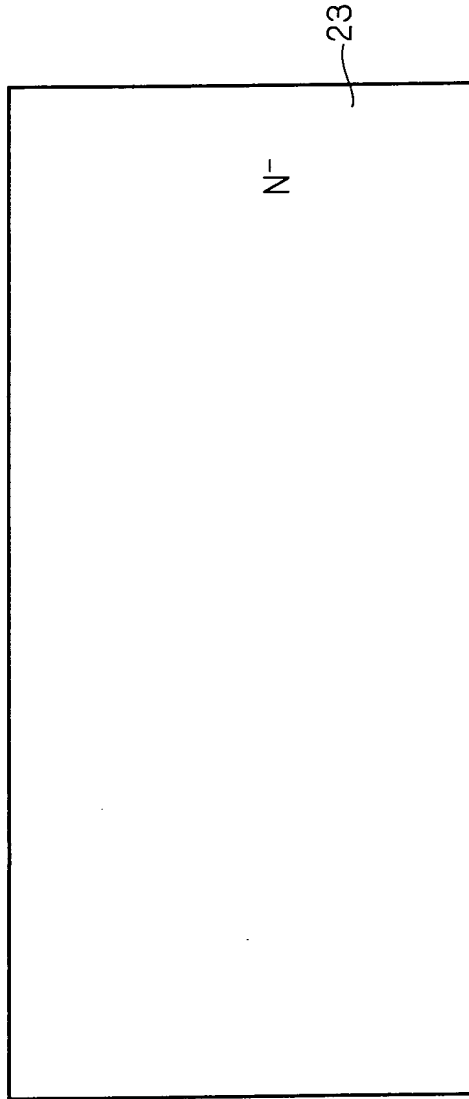


FIG. 12

FIG. 12



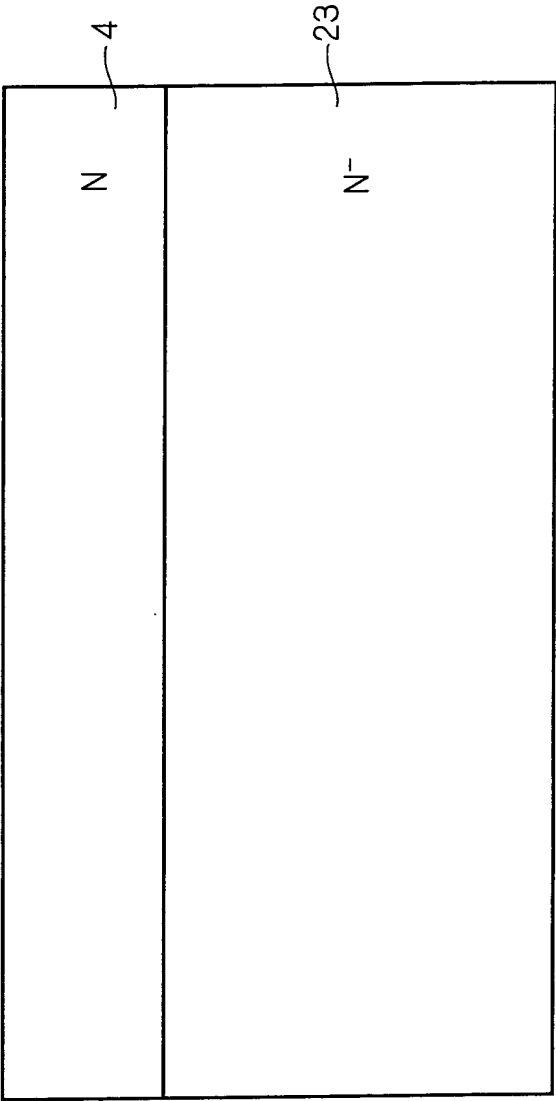


FIG. 13

FIG. 13

FIG. 14

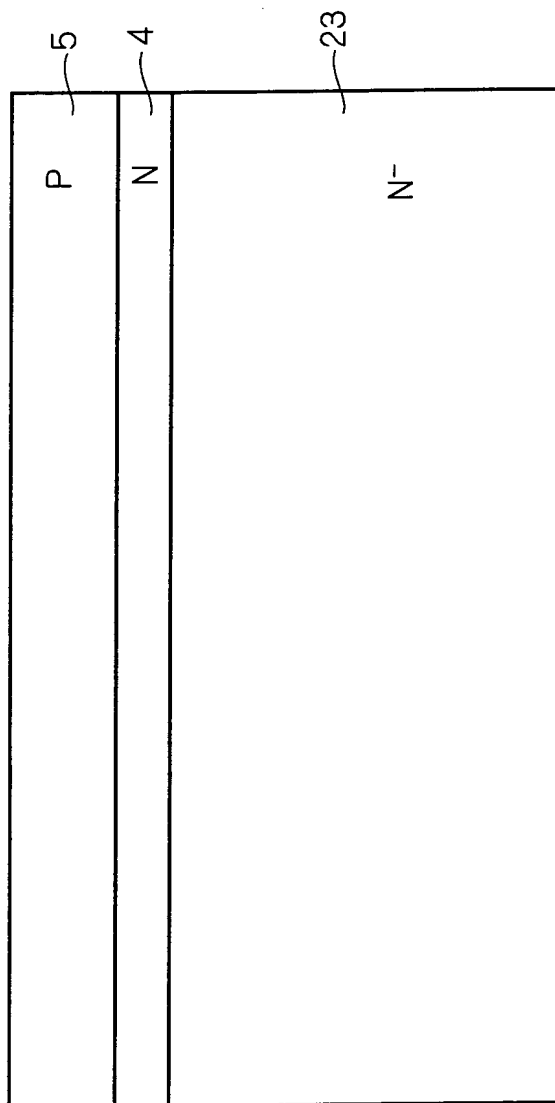


FIG. 15

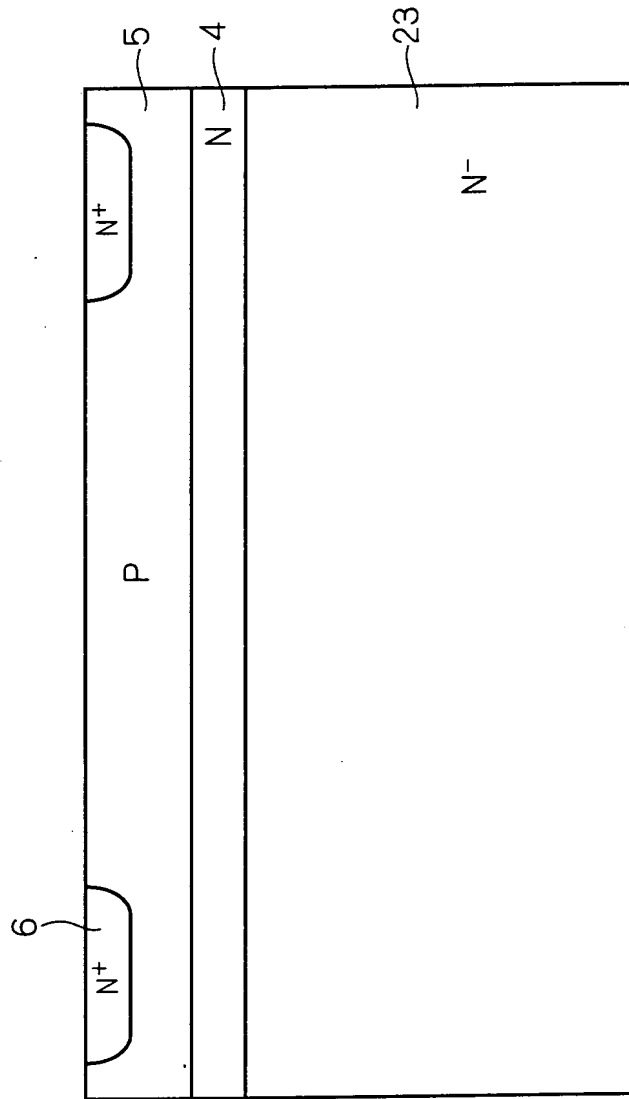


FIG. 16

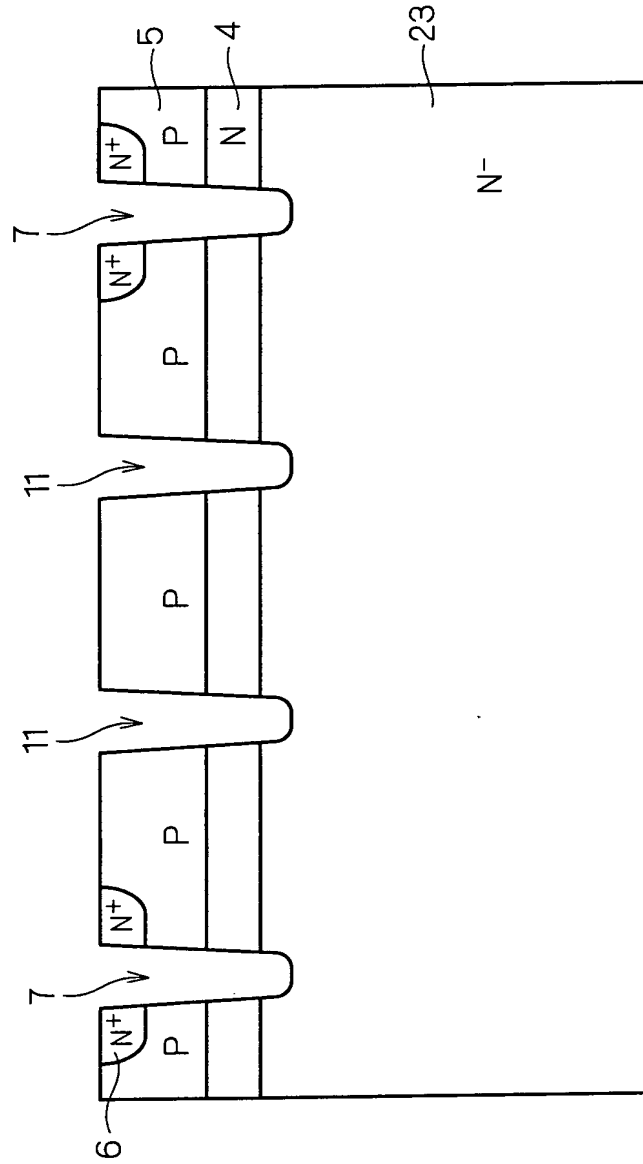


FIG. 17

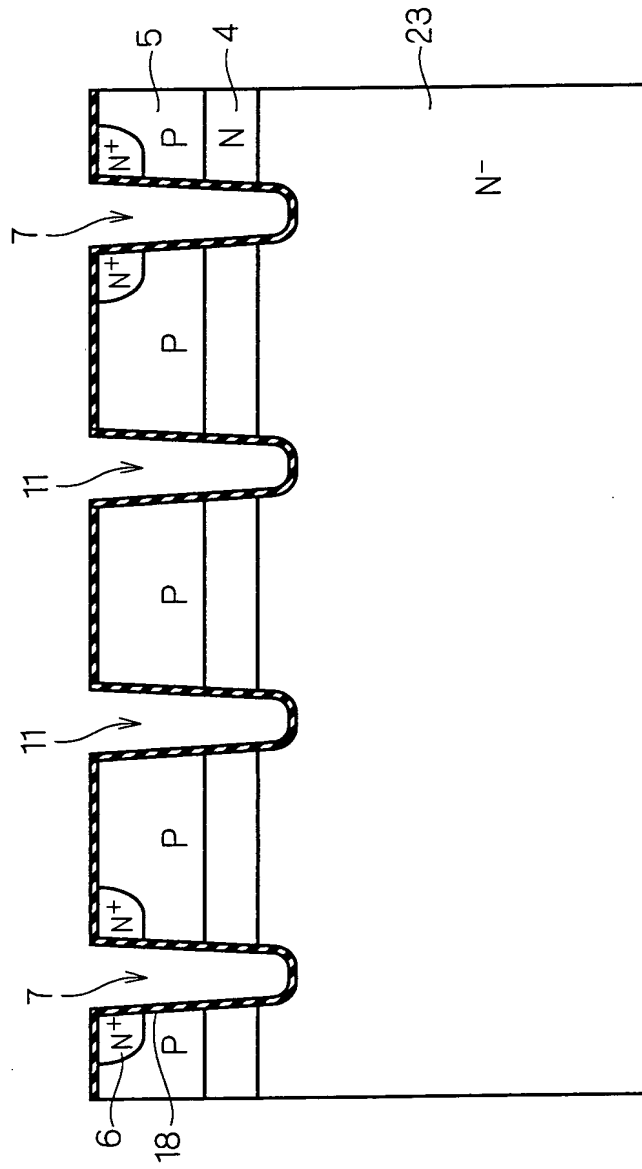


FIG. 18

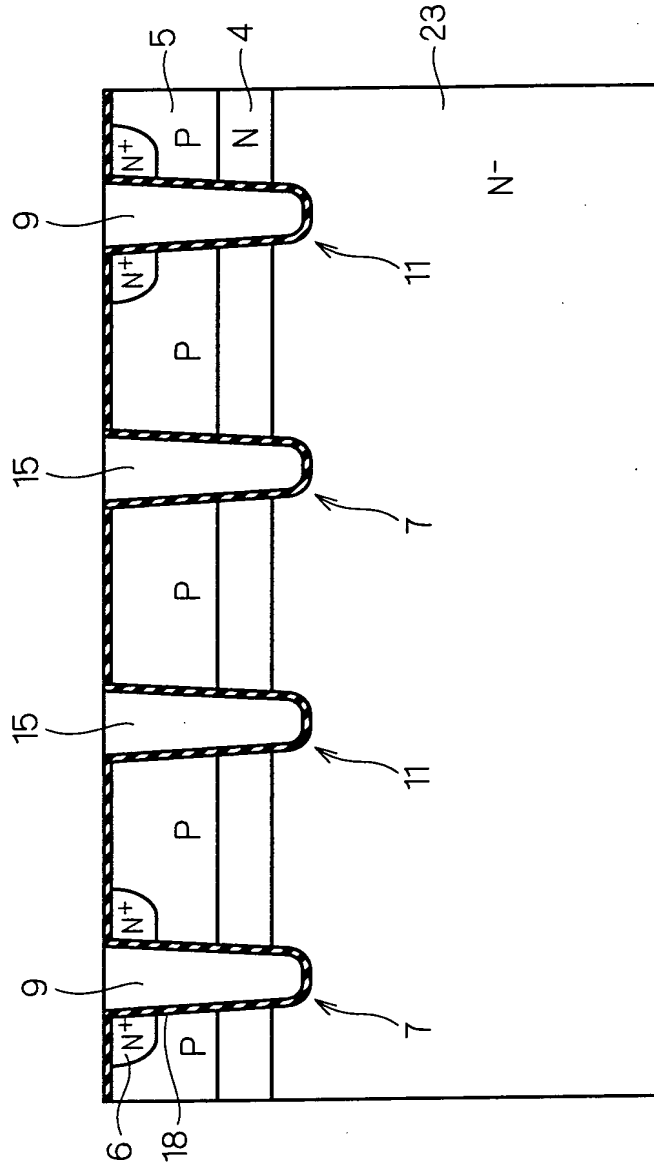
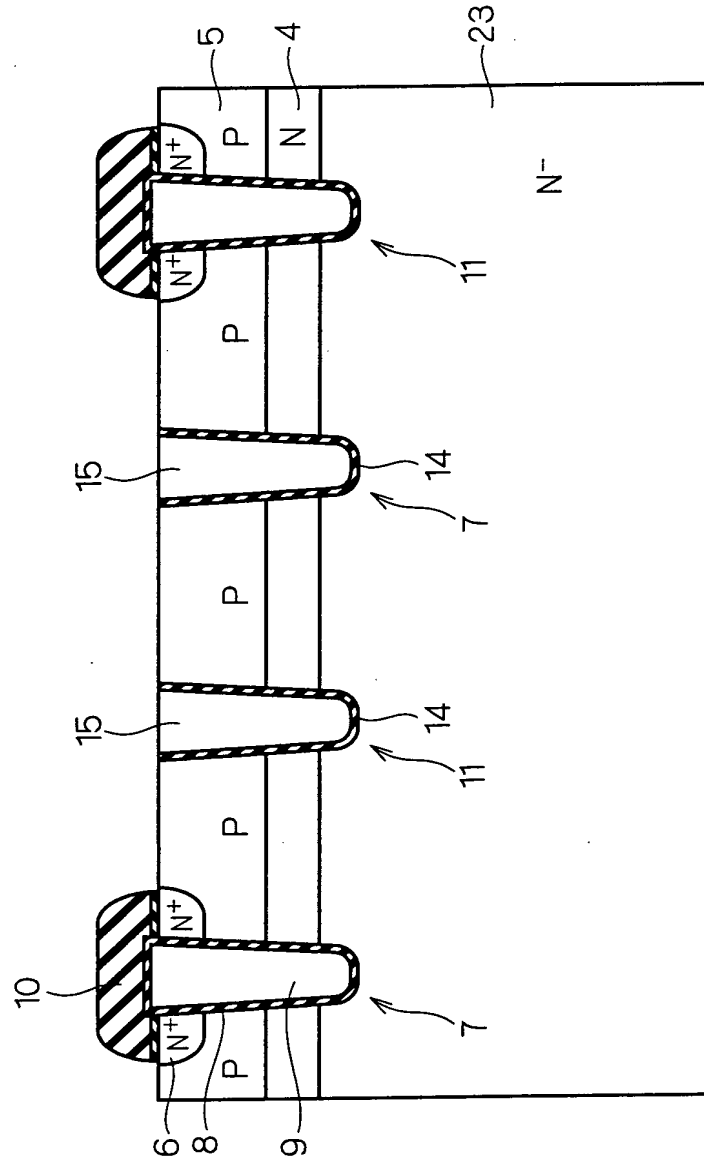
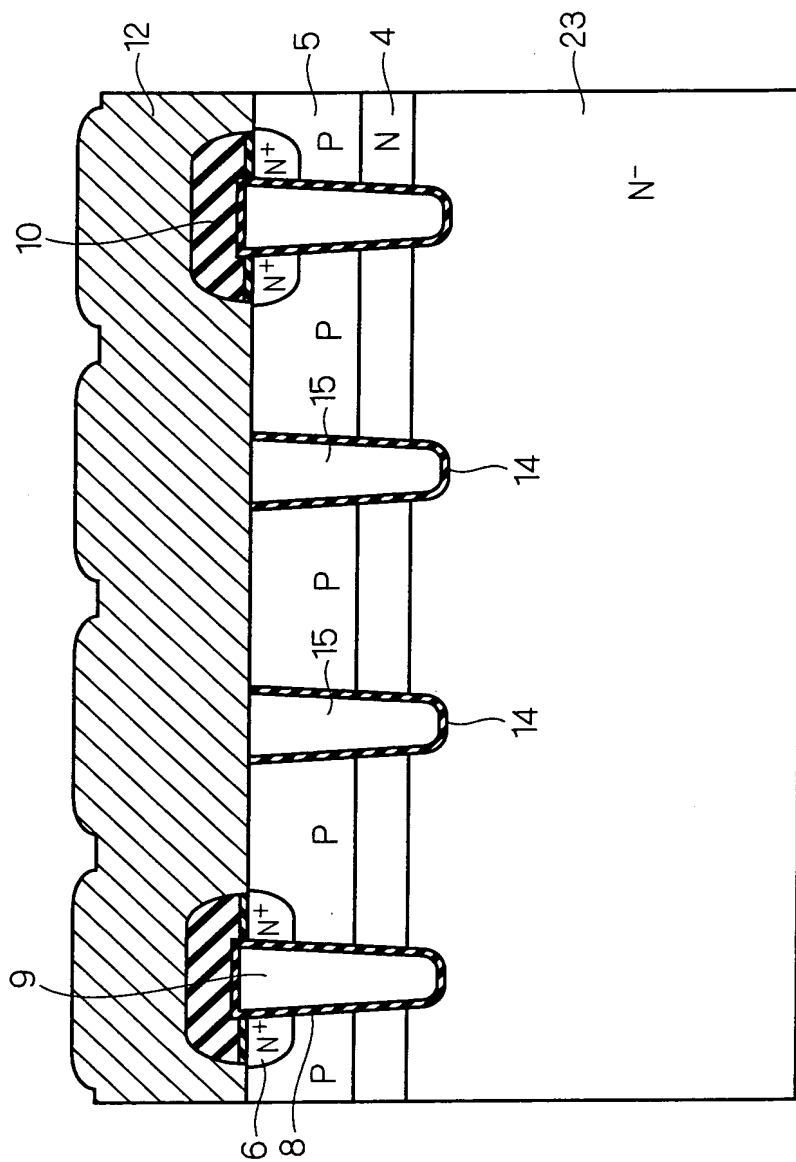


FIG. 19



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FIG. 20



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FIG. 21

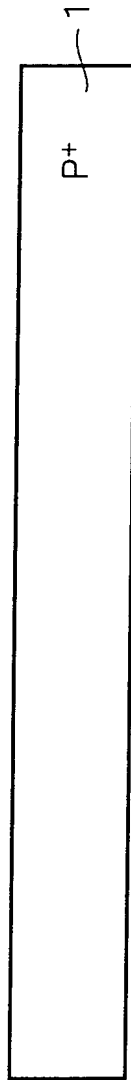
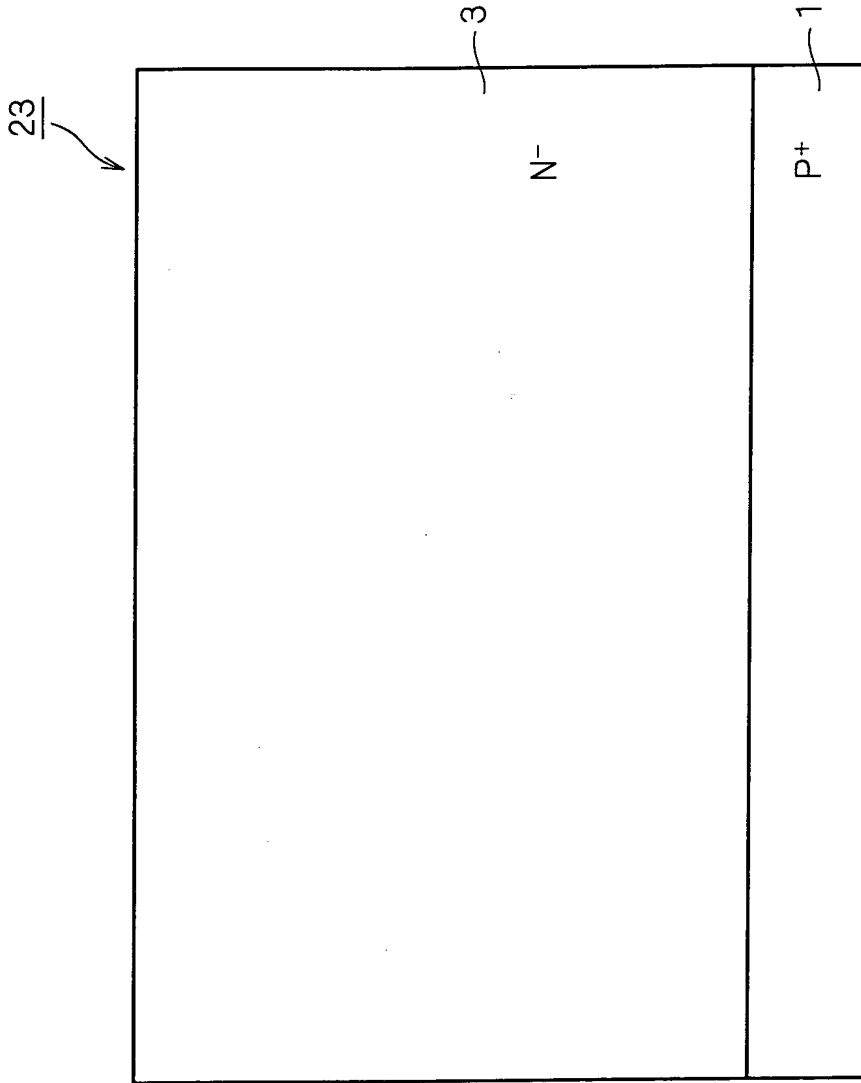
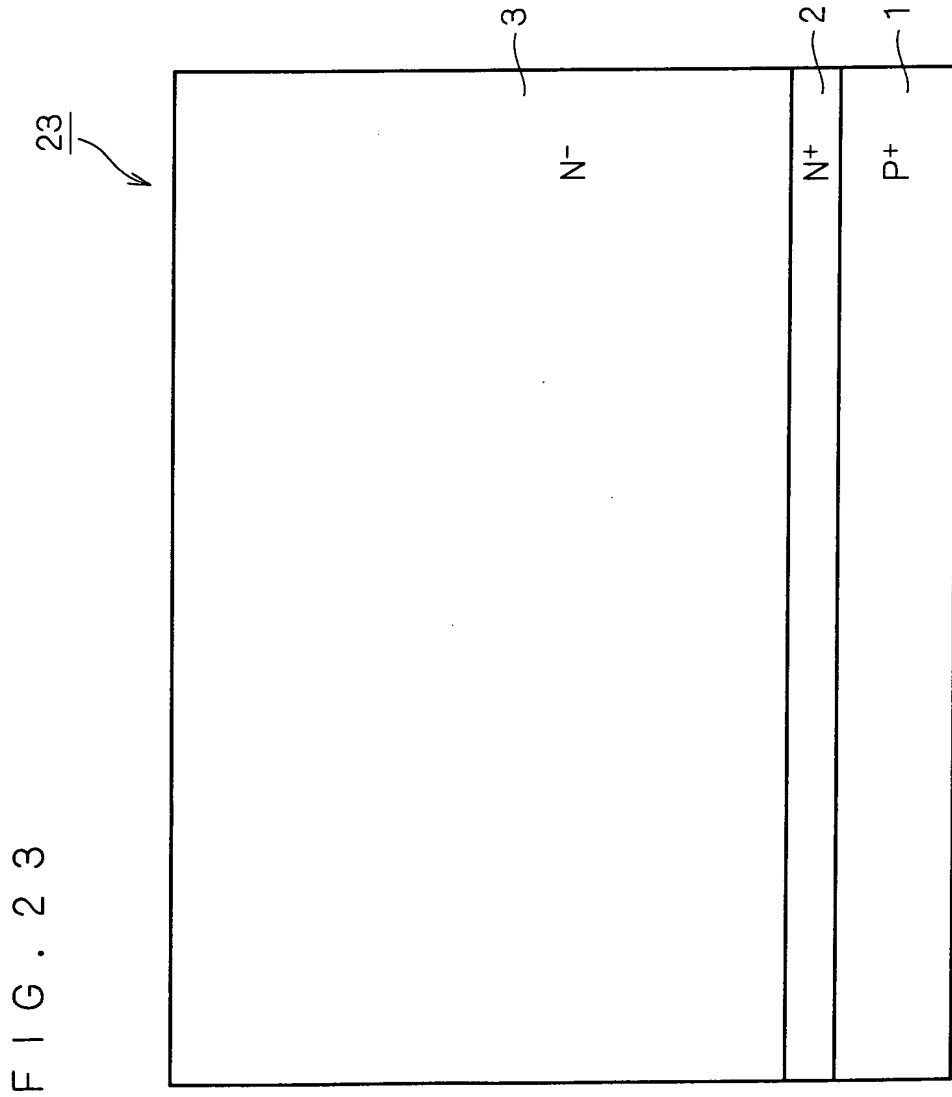


FIG. 22





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FIG. 24

FIG. 24

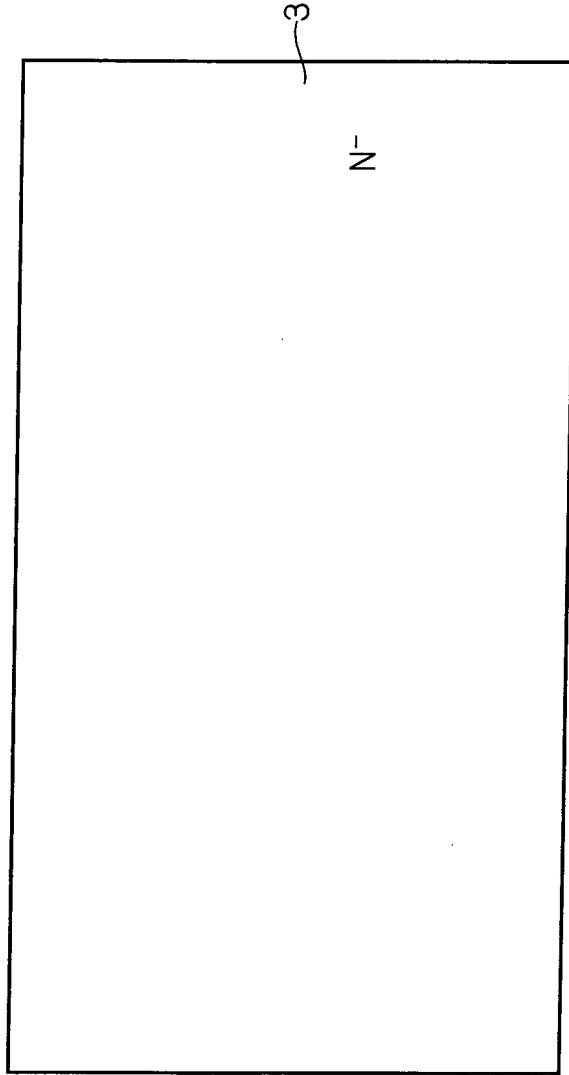
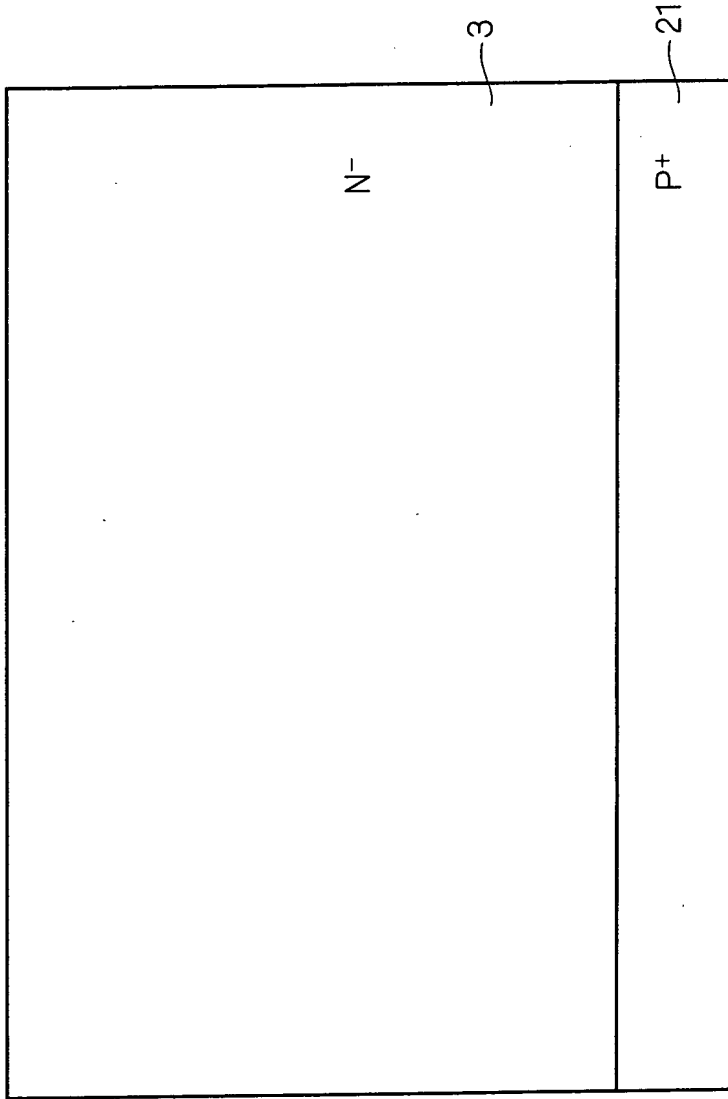


FIG. 25

FIG. 25

23



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FIG. 26

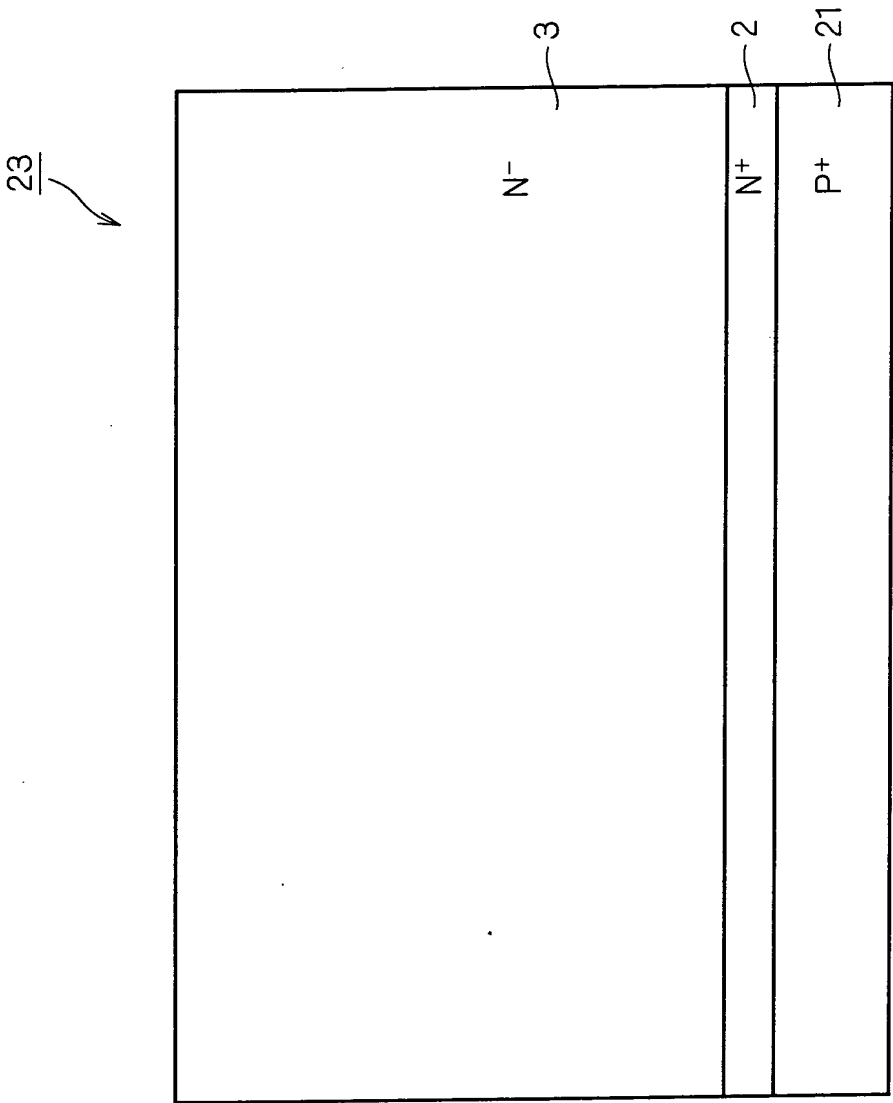
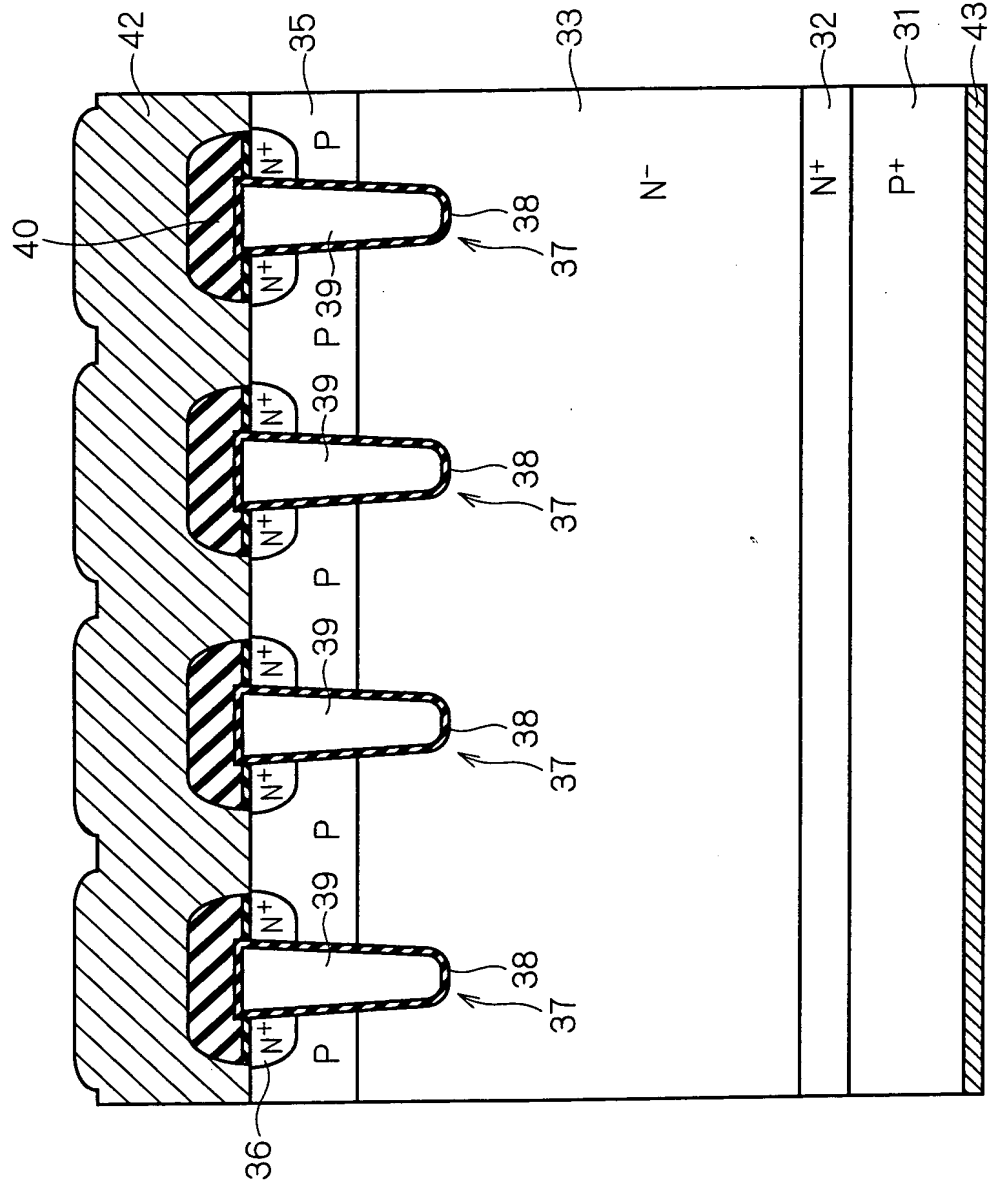


FIG. 27



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FIG. 28

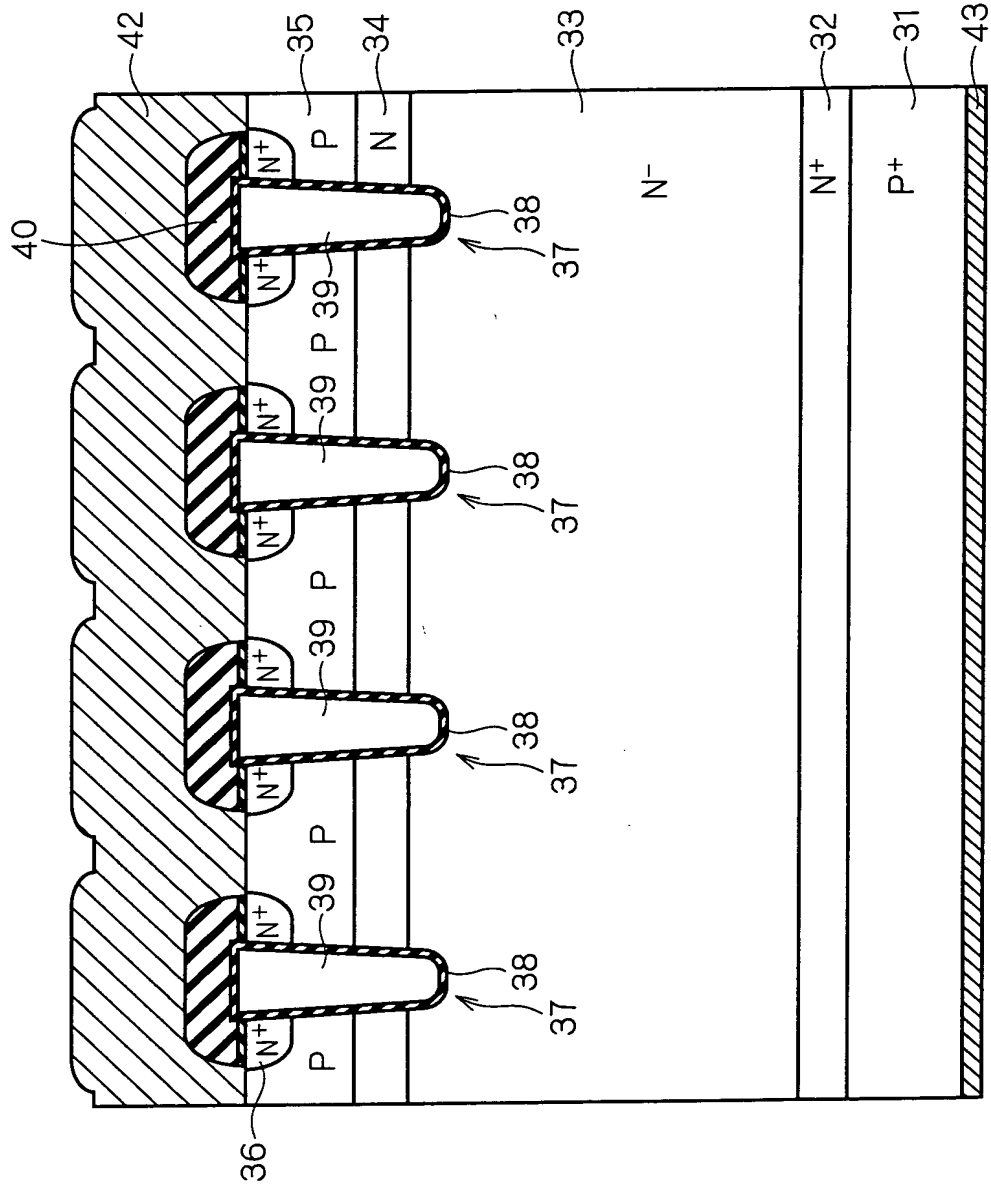
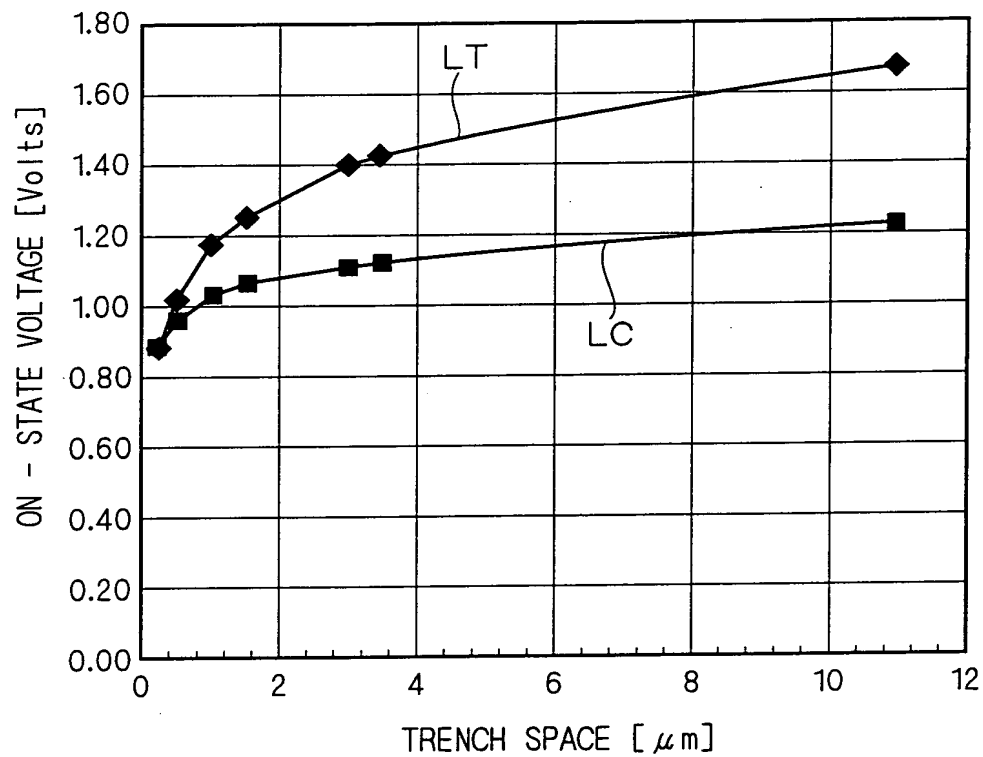


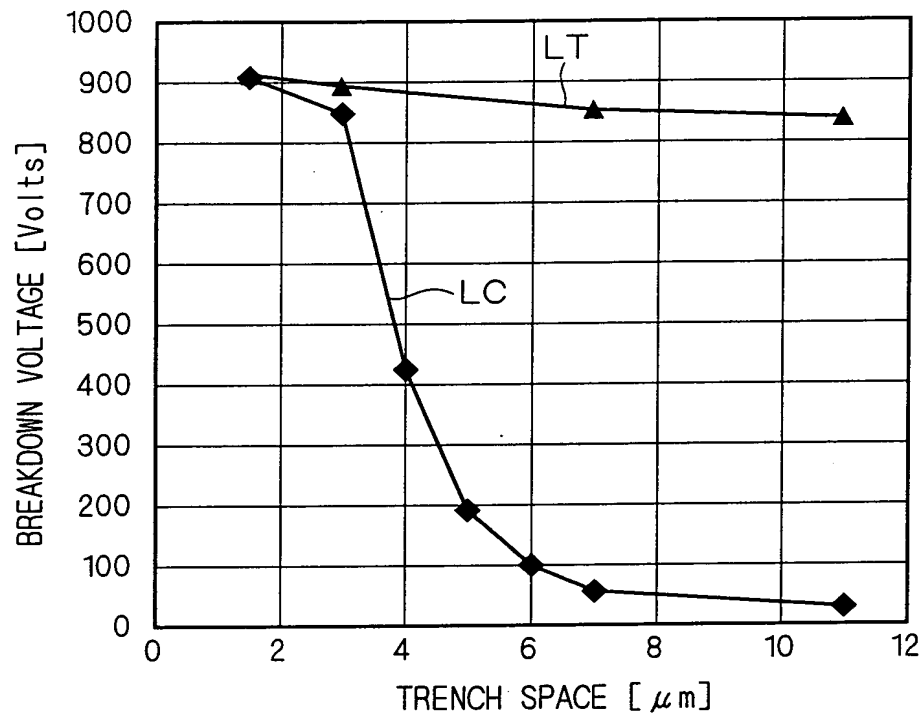
FIG. 28

FIG. 29



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[illegible]

FIG. 32

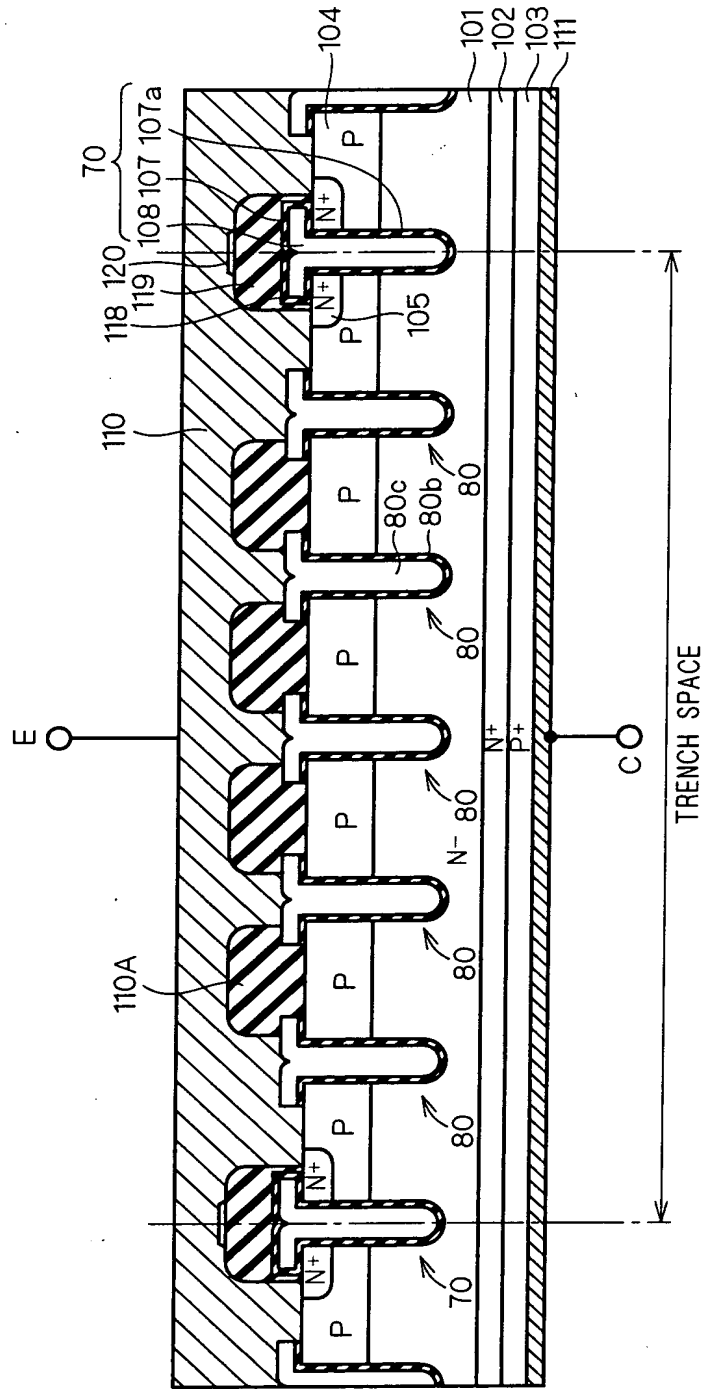


FIG. 32